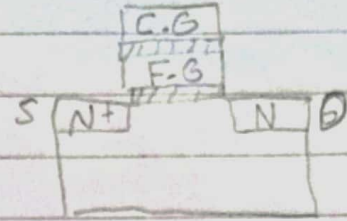


\* Non-volatile memory (ROM) "read only memory"

ROM  $\Rightarrow$  based on FGM "Floating gate mosfet"

negative "0" programming state  
 positive "1" erasing state



Mask Programmable ROM  
 PROM  
 EPROM

\* Mask Programmable ROM: (OTP) "one time program"

runtime لا يمكن تغييره بعد تصنيعه  
 ex: Tags, Bios chip

\* PROM: "Programmable ROM" OTP

\* EPROM: "erasable PROM"

أقصر أمد إلى 10 سنوات  
 radiation, noise لا يمكن تغييره  
 U.V. 30-5 دقائق

\* Hybrid memory:

EEPROM

Flash

NVRAM

RAM, ROM

(Read, write, non-volatile)

\* EEPROM: "electrical erasable programmable ROM"

Adv  $\Rightarrow$  electrical

endurance  $\rightarrow$  حتى 100,000

Byte access:

أقصر، أمد، access، بايت

dis adv  $\rightarrow$  high cost per bit

internal, external - لوجوده في MCU

communication Protocol  
 لوصف chip و MCU وتواصلهما

## ② Flash :

- Block access (sector by sector) <sup>من القطاع الى القطاع</sup>
- EEPROM
- Endurance  $\Rightarrow$  up to 10,000  $\times$
- low cost per bit

## ③ NVRAM : "non volatile RAM"

SRAM + Battery

SRAM + EEPROM + Battery <sup>غير متطاير</sup>

SRAM لا يحتاج الى بطارية EEPROM لا يحتاج الى بطارية

\* MIPS  $\Rightarrow$  million instruction per seconde

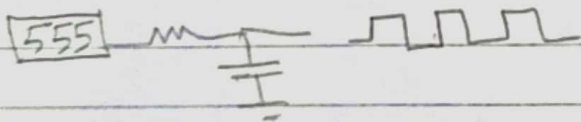
$\hookrightarrow$  assembly

square wave  $\leftarrow$  Clock  $\rightarrow$  signal  $\rightarrow$  F  $\rightarrow$  d  $\rightarrow$  e

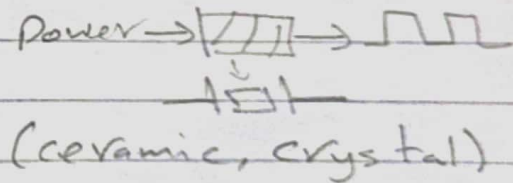
## clock systems

electrical

RC-oscillator



mechanical  
material



	RC	ceramic resonator	crystal oscillator
cost	lowest	in between	highest
accuracy	lowest	~	highest
setting time	highest	~	lowest
noise	low	high	high
Temp immunity	low	high	high
EMI	low	high	high
vibration	high	low	low